



Session Title	Interface Engineering/Epitaxy	Session Code	Fr-H2
Date and Time	2018-08-24 / 10:45 - 12:45		
Place	Room H		
Session Chair	TBA		

Fr-H2-1

10:45 - 11:00

Two-Dimensional Electron Gas Characteristics of AlGaN/GaN HEMTs with AlN Insert Layer on 4H-SiC Grown by MOCVD

Jaeyeon Han, Kyeongjae Lee, Uiho Choi, Yongjun Nam, Taehoon Jang, and Okhyun Nam
Korea Polytechnic Univ., Korea

Fr-H2-2

11:00 - 11:15

Selective Silicon Epitaxy via Plasma-Enhanced Chemical Vapor Deposition at Atmospheric Pressure

Hwayeon Ryu¹, Changhun Song¹, Hyunsu Shin¹, Seran Park¹, Won Ki Cho², Seung Jae Baik², Hoonjung Oh¹, and Dae-Hong Ko¹
¹Yonsei Univ., Korea, ²Hankyong Nat'l Univ., Korea

Fr-H2-3

11:15 - 11:30

BeCaZnO Quaternary Alloys: Epitaxial Film Growth and Ultraviolet Photodetector Fabrication

Teng Zhang, Mingkai Li, Yang Cheng, Wuzhong Zhang, Yinmei Lu, and Yunbin He
Hubei Univ., China

Fr-H2-4

11:30 - 11:45

The Properties of $Zr_xSn_{1-x}O_2$ Semiconductor Alloy Epitaxial Thin Film and its Application in Ultraviolet Photodetector

Yang Cheng, Mingkai Li, Debing Long, Jian Chen, Teng Zhang, Dongxue Meng, Yinmei Lu, and Yunbin He
Hubei Univ., China

Fr-H2-5

11:45 - 12:00

UV Detectors based on High-Quality $BexZn_{1-x}O_{1-y}S_y$ Alloy Films

Wuzhong Zhang, Mingkai Li, Yinmei Lu, Ronghuizi Yang, Teng Zhang, and Yunbin He
Hubei Univ., China

Fr-H2-6

12:00 - 12:15

Study of Atomic Arrangements and Charge Distribution on Si(001) Surfaces with the Adsorption of One Ge Atom by DFTB Calculations

Iin Zhang¹ and Lijun Wu²
¹Northeastern Univ., China, ²Shenyang Ligong Univ., China

Fr-H2-7

12:15 - 12:30

Luminescence and Photo-Transport Properties of GaN Nanowires

Shivesh Yadav, Swarup Deb, Kantimay D. Gupta, and Subhabrata Dhar
Indian Inst. of Tech. Bombay, India